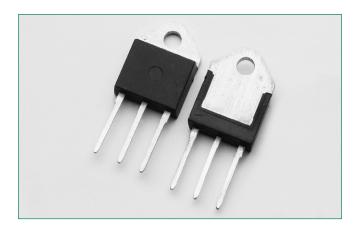


SK655KD





Description

Excellent unidirectional switches for phase control applications such as heating and motor speed controls.

Standard phase control SCRs are triggered with few milliamperes of current at less than 1.5V potential.

Features & Benefits

- RoHS compliant
- Voltage capability up to 1600 V
- Surge capability up to 520 A
- Electrically isolated package "KD-Package" and UL Recognized for 2500V_{RMS}
- UL Recognized as an Electrically Isolated Semiconductor Device to UL 1557.

Agency Recognitions

| Agency | Agency File Number |
|-------------|--------------------|
| 71 ° | E71639 |

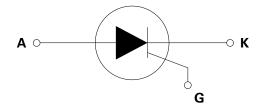
Applications

Typical applications are AC solid-state switches, industrial power tools and line rectification 50/60Hz.

Main Features

| Symbol | Value | Unit |
|------------------------------------|-------|------|
| I _{T(RMS)} | 55 | А |
| V _{DRM} /V _{RRM} | 1600 | V |
| I _{GT} | 70 | mA |

Schematic Symbol



Absolute Maximum Ratings

| Symbol | Parameter | Test Conditions | Value | Unit |
|------------------------------------|---|---|------------|------------------|
| V_{DRM}/V_{RRM} | Repetitive Peak off-state/Reverse Voltage | | 1600 | V |
| V _{DSM} /V _{RSM} | Non-repetitive peak off-state/Reverse voltage | | 1700 | V |
| I _{T(RMS)} | RMS on-state current | T _c = 55°C | 55 | А |
| I _{T(AV)} | Average on-state current | T _c = 55°C | 35 | А |
| | Peak non-repetitive surge current | single half cycle; f = 50Hz; T _J (initial) = 25°C | 550 | А |
| I _{TSM} | | single half cycle; f = 60Hz; T _J (initial) = 25°C | 660 | |
| l²t | I ² t Value for fusing | $t_{p} = 8.3 \text{ ms}$ | 1800 | A ² s |
| di/dt | Critical rate of rise of on-state current | | 150 | A/µs |
| I _{GM} | Peak gate current | T _J = 125°C | 3 | А |
| P _{G(AV)} | Average gate power dissipation | T _J = 125°C | 1 | W |
| T _{stg} | Storage temperature range | | -40 to 150 | °C |
| T _J | Operating junction temperature range | | -40 to 125 | °C |



Electrical Characteristics (T_J = 25°C, unless otherwise specified)

| Symbol | Test Conditions | Value | Unit | |
|-----------------|--|--|------|------|
| I _{GT} | V 12V P 20 0 | MAX. | 70 | mA |
| V _{GT} | $V_D = 12V; R_L = 30 \Omega$ | MAX. | 1.5 | V |
| dv/dt | $V_D = 2/3 V_{DRM}$; gate open; $T_J = 125$ °C | $V_D = 2/3 V_{DRM}$; gate open; $T_J = 125$ °C MIN. | | V/µs |
| $V_{\sf GD}$ | $V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$; $T_J = 125^{\circ}\text{C}$ MIN. | | 0.2 | V |
| I _H | I _T = 500mA (initial) | MAX. | 200 | mA |
| t _q | I_{τ} =0.5A; t_{ρ} =50μs; dv/dt=5V/μs; di/dt=-30A/μs | TYP. | 20 | μs |
| t _{gt} | $I_{G} = 2 \times I_{GT}$; PW = 15 μ s; $I_{T} = 110A$ | TYP. | 5 | μs |

Static Characteristics

| Symbol | Test Conditions | | Value | Unit | |
|-------------------------------------|--|------------------------|-------|------|----|
| V_{TM} | $I_{_{ m T}} = 110 \text{A}; \ t_{_{ m p}} = 380 \mu \text{s}$ | | MAX. | 1.8 | V |
| 1 /1 | V (V | T _J = 25°C | NAAV | 10 | μА |
| I _{DRM} / I _{RRM} | V_{DRM}/V_{RRM} | T _J = 125°C | MAX. | 8 | mA |

Thermal Resistances

| Symbol | Parameter | Value | Unit |
|-------------------|-----------------------|-------|------|
| R _{euci} | Junction to case (AC) | 1.0 | °C/W |

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

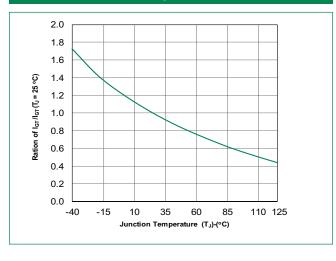
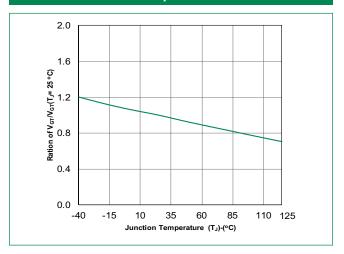


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature





Thyristors 55 Amp Standard SCRs

Figure 3: Normalized DC Holding Current vs. Junction Temperature

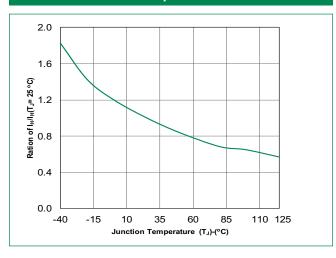


Figure 4: On-State Current vs. On-State Voltage (Typical)

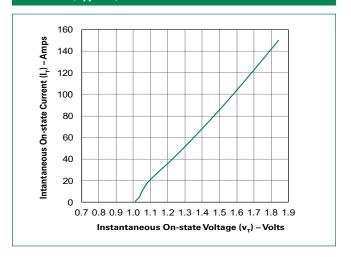


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

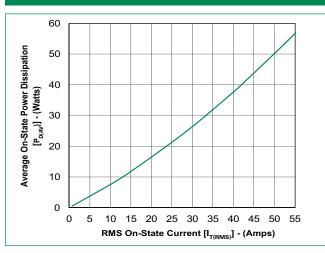


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

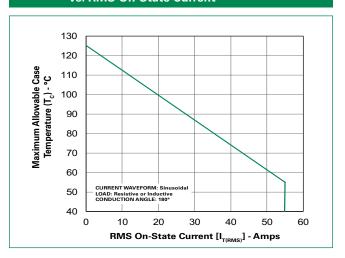


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

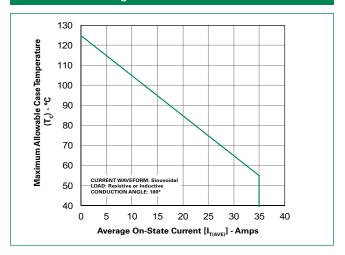
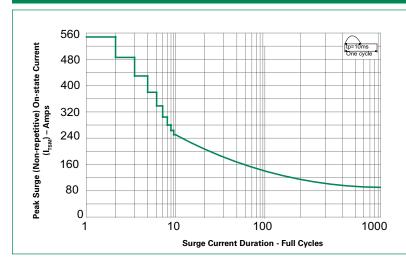




Figure 8: Surge Peak On-State Current vs. Number of Cycles



SUPPLY FREQUENCY: 50 Hz Sinusoidal

LOAD: Resistive

RMS On-State Current: [$I_{T(RMS)}$]: Maximum Rated Value at Specified Case Temperature

Notes:

- 1. Gate control may be lost during and immediately following surge current interval.
- Overload may not be repeated until junction temperature has returned to steady-state rated value.

Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

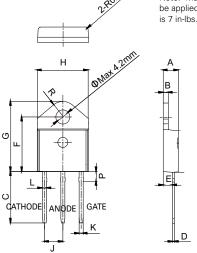
Environmental Specifications

| Test | Specifications and Conditions |
|---------------------------|---|
| AC Blocking | JESD22-A108C, 80% V _{DRM} @125°C for 168 hours |
| Temperature Cycling | JESD22-A104D, M-1051, 50 cycles; -50°C to +150°C; 15-min dwell-time |
| Temperature/Humidity | EIA / JEDEC, JESD22-A101 168 hours; 100V - DC: 85°C; 85% rel humidity |
| Resistance to Solder Heat | JESD22-B106C |
| Solderability | ANSI/J-STD-002, category 3, Test A |

Physical Specification

| Terminal Finish | 100% Matte Tin-Plated |
|-----------------|--|
| Body Material | UL Recognized compound meeting flammability rating V-0 |

Dimensions - TO-218AC (KD Package) - Isolated Mounting Tab Common with Center Lead



Note: Maximum torque to be applied to mounting tab is 7 in-lbs. (0.8 Nm).

| Dimension | willimeters | | | inches | | |
|-----------|-------------|------|-------|--------|-------|-------|
| Dimension | Min. | Тур. | Max. | Min. | Тур. | Max. |
| Α | 4.40 | | 4.60 | 0.173 | | 0.181 |
| В | 1.45 | | 1.55 | 0.057 | | 0.061 |
| С | 14.35 | | 15.60 | 0.565 | | 0.614 |
| D | 0.50 | | 0.70 | 0.020 | | 0.028 |
| E | 2.70 | | 2.90 | 0.106 | | 0.114 |
| F | 15.80 | | 16.50 | 0.622 | | 0.650 |
| G | 20.40 | | 21.10 | 0.803 | | 0.831 |
| Н | 15.10 | | 15.50 | 0.594 | | 0.610 |
| J | 5.40 | | 5.65 | 0.213 | | 0.222 |
| К | 1.10 | | 1.40 | 0.043 | | 0.055 |
| L | 1.35 | | 1.50 | 0.053 | | 0.059 |
| P | 2.80 | | 3.00 | 0.110 | | 0.118 |
| R | | 4.35 | | | 0.171 | |

Thyristors 55 Amp Standard SCRs

Product Selector

| Part Number | Gate Sensitivity | Туре | Package |
|-------------|------------------|--------------|----------|
| SK655KD | 70mA | Standard SCR | TO-218AC |

Packing Options

| Part Number | Marking | Weight | Packing Mode | Base Quantity |
|-------------|---------|--------|--------------|--------------------|
| SK655KDTP | SK655KD | 4.8g | Tube | 3600 (30 per tube) |

Part Numbering System

S K6 55 KD TP Device Type S: SCR Packaging Type TP: Tube Pack Voltage Rating K2: 1200V K6: 1600V Current Rating S5: 55A Package Type KD: T0-218AC (isolated)

Part Marking System

